

Clean Copy of Amended Claim

1. (Amended) A high voltage semiconductor device, comprising:
- a high concentration collector area of a first conductive type;
 - a low concentration collector area of a first conductive type formed on the high concentration collector area;
 - a base area of a second conductive type formed on the low concentration collector area and having a trench which penetrates the low concentration collector area in a vertical direction at a junction termination;
 - a high concentration emitter area of a first conductive type formed on a predetermined upper surface of the base area; and
 - an emitter electrode, a base electrode, and a collector electrode isolated from one another and connected to the emitter area, the base area, and the collector area, respectively,
- wherein the depth of the trench is 50-150 μm .
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